

REMARKS

Reconsideration of the instant application and favorable action are solicited. In order to more particularly point out and distinct claim that which the applicants regard
5 as their invention, claim 1 has been amended in this RCE. No new matter is introduced.

1. Request for Continued Examination:

The applicants respectfully request continued examination of the above-indicated application as per 37 CFR 1.114.

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2. Amendment to claim 1:

In claim 1, the step: "performing a seventh and eighth ion implantation processes to implant ions of the first conductivity type into the second ion well and implant ions of the second conductivity type into the first ion well, thereby forming a
15 first channel stop regions within the high-voltage device area" has been replaced with two steps: "performing a seventh ion implantation processes to implant ions of the first conductivity type into the first ion well to form a first channel stop region within the high-voltage device area" and "performing an eighth ion implantation processes to implant ions of the second conductivity type into the second ion well to form a second
20 channel stop region within the high-voltage device area".

Applicants would like to use "first channel stop region" and "second channel stop region" of the amended claim 1 to represent regions 186 and 182 respectively through FIGS. 13-18.

The step: "performing a ninth ion implantation process to form a second channel
25 stop region in the fourth ion well within the low-voltage device area" has been changed to "performing a ninth ion implantation process in the fourth ion well within the low-voltage device area to form an anti-punch-through doping region in the fourth ion well".

Applicants believe that the prior art, either singly or in combination fails to
30 anticipate or render obvious the limitations of the once amended claim 1.

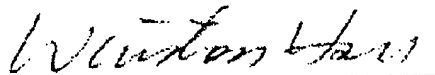
Reconsideration of claim 1 is respectfully requested.

As claims 2-5 are dependent upon claim 1, they should be allowable if claim 1 is

allowed. Reconsideration of claims 2-5 is therefore politely requested.

Sincerely yours,

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